

FORM PTO-1449		Atty. Docket No. XA-10191	Appln. No. 10/511541
<u>LIST OF DOCUMENTS CITED BY APPLICANT</u>		Applicant KOSHIMIZU, Makoto et al.	
		Filing Date Herewith	Group Art Unit 2812

U.S. PATENT DOCUMENTS

Examiner Initial		Document Number	Date	Name	Class	Sub-class	Filing Date
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						

FOREIGN PATENT DOCUMENTS

Examiner Initial		Document Number	Date	Country	Class	Sub-class	Translation
KL	AH	2705344	10/09/97	Japan			Abstract
KL	AI	10-092833	04/10/98	Japan			
KL	AJ	63-052412	03/05/88	Japan			
KL	AK	06-151387	05/31/94	Japan			
KL	AL	11-176807	07/02/99	Japan			
	AM						
	AN						
	AO						
	AP						
	AQ						
	AR						
	AS						

OTHER (including author, title, date, pertinent pages, etc.)

KL	AT	F. Sato et al., "A super self-aligned selectively grown SiGe base (SSSB) bipolar transistor fabricated by cold-wall UHV/CVD technology", IEEE Trans. ED, Vol. 41, Issue 8, August 1994, pp. 1373-1378. (Abstract Only)
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Examiner <i>[Signature]</i> Kyoung Lee	Date Considered 3/14/06
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.